We have developed 65nm-node CMOS technology for general-purpose system-on-a-chip, in which both standby and active power reductions are strongly required. With highly reliable triple gate oxide and optimized RTA condition, an average standby current can be reduced to one-fifth compared with conventional case. High-speed and low-gate-leakage transistors show on-current (n/p) of 680/240µA/µm with $I_{ON}$ 13nA/µm and $I_{OFF}$ 30nA/µm and of 490/175µA/µm with $I_{ON}$ 0.8nA/µm and $I_{OFF}$ 3nA/µm, simultaneously. Gate oxide of all the above transistors exhibit tight TDDB distributions.